

isc Silicon NPN Power Transistor

2SD1032

DESCRIPTION

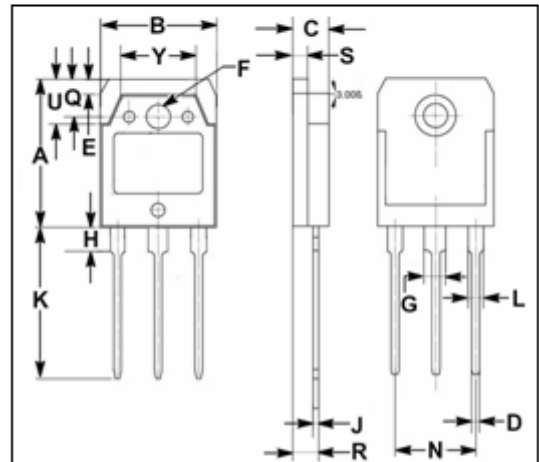
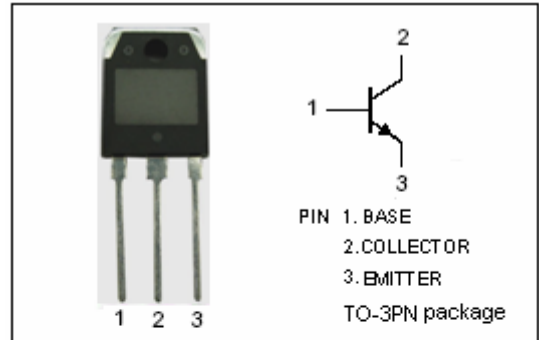
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V(\text{Min})$
- Large Collector Power Dissipation
- Complement to Type 2SB812

APPLICATIONS

- Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA}; I_B=0$	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$			1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=4\text{V}$			2	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=30\text{V}; I_B=0$			700	μA
I_{CES}	Collector Cutoff Current	$V_{CE}=60\text{V}; V_{BE}=0$			400	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=4\text{V}$	40		250	
h_{FE-2}	DC Current Gain	$I_C=3\text{A}; V_{CE}=4\text{V}$	15			

Switching times

t_{on}	Turn-On Time	$I_C=4\text{A}, I_{B1}=-I_{B2}=0.4\text{A}$		0.2		μs
t_{off}	Turn-Off Time			1.4		μs

◆ h_{FE-1} Classifications

R	Q	P
40-90	70-150	120-250